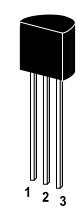
PNP Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into two groups, O and Y according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	35	V
Collector Emitter Voltage	-V _{CEO}	30	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	800	mA
Emitter Current	Ι _Ε	800	mA
Power Dissipation	P _{tot}	600	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







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ST 2SA1271

Characteristics at T_{amb}=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at -V _{CE} =1V, -I _C =100mA					
Current Gain Group O	h _{FE}	100	-	200	-
Y	h _{FE}	160	-	320	-
at $-V_{CE}=1V$, $-I_{C}=700$ mA	h _{FE}	35	-	-	-
Collector Cutoff Current					
at -V _{CB} =35V	-I _{CBO}	-	-	0.1	μA
Emitter Cutoff Current					
at -V _{EB} =5V	-I _{EBO}	-	-	0.1	μA
Collector Emitter Saturation Voltage					
at -I _C =500mA, -I _B =20mA	-V _{CE(sat)}	-	-	0.7	V
Transition Frequency					
at -V _{CE} =5V, -I _C =10mA	f⊤	-	120	-	MHz
Base Emitter Voltage					
at -I _C =10mA, -V _{CE} =1V	-V _{BE}	0.5	-	0.8	V
Collector Output Capacitance					
at -V _{CB} =10V, f=1MHz	C _{OB}	-	19	-	pF
Collector Emitter Breakdown Voltage					
at -I _c =10mA	-V _{CEO}	30	-	-	V







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